

L Number	Hits	Search Text	DB	Time stamp
4	6	("4975874" "5222038" "5341326" "5369612" "5463577" "5650972").PN.	USPAT	2004/04/18 19:46
5	2	("6396088").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 19:48
6	4	("4975874" "5222038" "5463577" "5559350").PN.	USPAT	2004/04/18 19:47
7	2	("6288925").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 19:49
8	3	("4975874" "5222038" "5463577").PN.	USPAT	2004/04/18 19:48
9	1	6288925.URPN.	USPAT	2004/04/18 19:48
10	2	("6069813").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 19:50
11	2	("5222038" "5463577").PN.	USPAT	2004/04/18 19:49
12	0	6069813.URPN.	USPAT	2004/04/18 19:49
13	2	("6115279").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 19:50
14	3	6115279.URPN.	USPAT	2004/04/18 19:50
15	9	("4673966" "5119169" "5391900" "5598348" "5914873" "6028440" "6057169" "6115279" "6202196").PN.	USPAT	2004/04/18 19:52
-	2	("4975874").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:33
-	4	("5222038").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 13:54
-	3	("5463577").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 14:54
-	2	("6288925").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 14:12
-	3	("4975874" "5222038" "5463577").PN.	USPAT	2002/06/16 14:10
-	1	6288925.URPN.	USPAT	2002/06/16 14:11
-	2	("6069813").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 14:13
-	2	("5222038" "5463577").PN.	USPAT	2002/06/16 14:12
-	0	6069813.URPN.	USPAT	2002/06/16 14:12
-	0	6069813.URPN.	USPAT	2002/06/16 14:12
-	2	("5953242").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 14:14
-	2	("5222038" "5463577").PN.	USPAT	2002/06/16 14:13

-	0	5953242.URPN.	USPAT	2002/06/16 14:13
-	2	("6115279").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 14:14
-	3	("4975874" "5388068" "5650972").PN.	USPAT	2002/06/16 14:14
-	2	("4803664" "5084842").PN.	USPAT	2002/06/16 14:42
-	4	("5309393" "5317540" "5341326" "5369612").PN.	USPAT	2002/06/16 14:44
-	2461	semiconductor and memory and ((bit adj line) with crosses)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 14:56
-	373	(semiconductor and memory and ((bit adj line) with crosses)) and MOSFET	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 15:06
-	10	((semiconductor and memory and ((bit adj line) with crosses)) and MOSFET) and (MOSFET with (active adj region))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 15:04
-	1	((semiconductor and memory and ((bit adj line) with crosses)) and MOSFET) and (MOSFET with (active adj region))) and H-shaped	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 15:04
-	56	((semiconductor and memory and ((bit adj line) with crosses)) and MOSFET) and (second with (conductive adj layer))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 15:16
-	19	((semiconductor and memory and ((bit adj line) with crosses)) and MOSFET) and (second with (conductive adj layer))) and (sense adj amplifier)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 15:16
-	1815	257/296.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 16:46
-	1915	365/189.05.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 17:39
-	359	365/189.12.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/17 09:45
-	946	365/207.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 18:17
-	1797	365/149.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/17 09:46
-	13	"0281868"	DERWENT	2002/09/08 15:18
-	1	2000JP-0281868	DERWENT	2002/09/08 15:20
-	4	"239913"	DERWENT	2002/09/08 15:21
-	6	"281868"	DERWENT	2002/09/08 16:10
-	179	257/287.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/09/08 16:11
-	153	257/307.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/09/08 16:11

-	2	("6512257").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 19:47
-	6	("4975874" "5222038" "5341326" "5369612" "5463577" "5650972").PN.	USPAT	2004/04/14 16:24
-	11	5650972.URPN.	USPAT	2004/04/14 14:55
-	16	5369612.URPN.	USPAT	2004/04/14 14:55
-	19	5341326.URPN.	USPAT	2004/04/14 15:47
-	162	257/333.ccls.	USPAT	2004/04/14 16:24
-	2297	257/296.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 16:46
-	2271	365/189.05.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 18:09
-	435	365/189.12.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 18:09
-	1175	365/207.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 18:39
-	2036	365/149.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/14 18:39
-	22	semiconductor and memory and bit and (MOS or MOSFET) and ((active adj region) with (T-shaped or H-shaped))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/04/15 10:59
-	5	("5404030" "5691561" "5973369" "6081016" "6160298").PN.	USPAT	2004/04/15 10:59